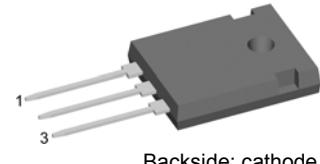
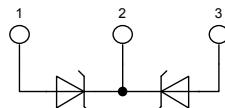


Schottky Diode Gen 2

High Performance Schottky Diode
Low Loss and Soft Recovery
Common Cathode

Part number

DSA 50 C 100 HB



Backside: cathode

Features / Advantages:

- Very low V_f
- Extremely low switching losses
- low I_{rm} values
- Improved thermal behaviour
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching

Applications:

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Package:

- Housing: TO-247
- Industry standard outline
- Epoxy meets UL 94V-0
- RoHS compliant

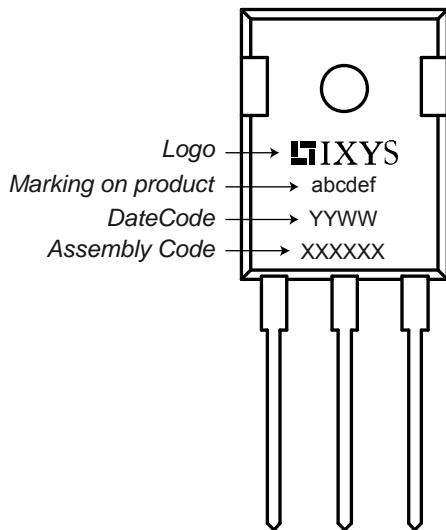
Symbol	Definition	Conditions			Ratings		
					min.	typ.	max.
V_{RRM}	max. repetitive reverse voltage			$T_{VJ} = 25^\circ\text{C}$			100
I_R	reverse current	$V_R = 100\text{ V}$		$T_{VJ} = 25^\circ\text{C}$		0.45	mA
		$V_R = 100\text{ V}$		$T_{VJ} = 125^\circ\text{C}$		5	mA
V_F	forward voltage	$I_F = 25\text{ A}$		$T_{VJ} = 25^\circ\text{C}$		0.90	V
		$I_F = 50\text{ A}$				1.07	V
		$I_F = 25\text{ A}$		$T_{VJ} = 125^\circ\text{C}$		0.72	V
		$I_F = 50\text{ A}$				0.90	V
I_{FAV}	average forward current	rectangular	$d = 0.5$	$T_c = 155^\circ\text{C}$			25
V_{FO} r_F	threshold voltage slope resistance } for power loss calculation only			$T_{VJ} = 175^\circ\text{C}$		0.45	V
						7.3	mΩ
R_{thJC}	thermal resistance junction to case					0.95	K/W
T_{VJ}	virtual junction temperature				-55	175	°C
P_{tot}	total power dissipation			$T_c = 25^\circ\text{C}$		160	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms}$ (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		230	A
C_J	junction capacitance	$V_R = 12\text{ V}; f = 1\text{ MHz}$		$T_{VJ} = 25^\circ\text{C}$	289		pF

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
I_{RMS}	RMS current	per pin ¹⁾			50	A
R_{thCH}	thermal resistance case to heatsink			0.25		K/W
T_{stg}	storage temperature		-55		150	°C
Weight				6		g
M_D	mounting torque		0.8		1.2	Nm
F_c	mounting force with clip		20		120	N

¹⁾ I_{RMS} is typically limited by: 1. pin-to-chip resistance; or by 2. current capability of the chip.

In case of 1, a common cathode/anode configuration and a non-isolated backside, the whole current capability can be used by connecting the backside.

Product Marking



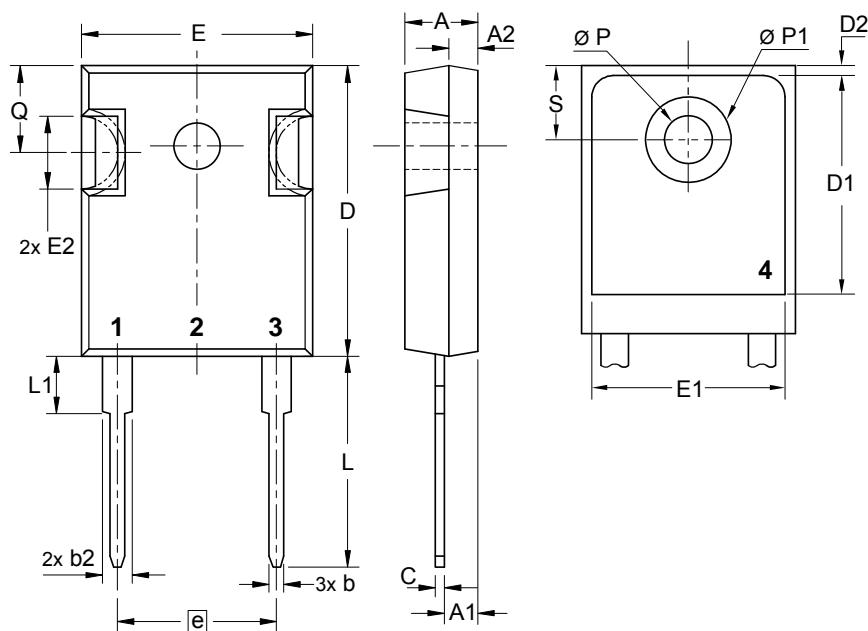
Part number

D = Diode
 S = Schottky Diode
 A = low VF
 50 = Current Rating [A]
 C = Common Cathode
 100 = Reverse Voltage [V]
 HB = TO-247AD (3)

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Code Key
Standard	DSA 50 C 100 HB	DSA50C100HB	Tube	30	502774

Similar Part	Package	Voltage class
DSA50C100QB	TO-3P (3)	100
DSA60C100PB	TO-220AB (3)	100

Outlines TO-247



Sym.	Inches min. max.	Millimeter min. max.
A	0.185 0.209	4.70 5.30
A1	0.087 0.102	2.21 2.59
A2	0.059 0.098	1.50 2.49
D	0.819 0.845	20.79 21.45
E	0.610 0.640	15.48 16.24
E2	0.170 0.216	4.31 5.48
e	0.430 BSC	10.92 BSC
L	0.780 0.800	19.80 20.30
L1	- 0.177	- 4.49
Ø P	0.140 0.144	3.55 3.65
Q	0.212 0.244	5.38 6.19
S	0.242 BSC	6.14 BSC
b	0.039 0.055	0.99 1.40
b2	0.065 0.094	1.65 2.39
b4	0.102 0.135	2.59 3.43
c	0.015 0.035	0.38 0.89
D1	0.515 -	13.07 -
D2	0.020 0.053	0.51 1.35
E1	0.530 -	13.45 -
Ø P1	- 0.29	- 7.39

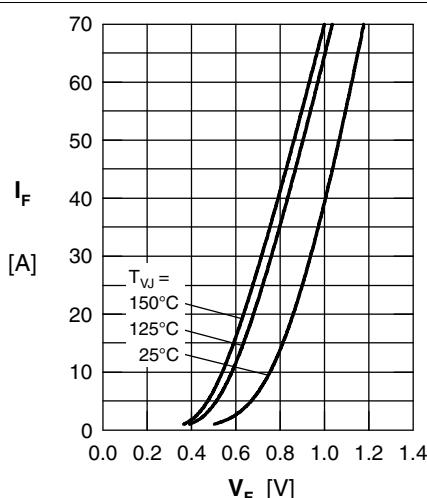


Fig. 1 Maximum forward voltage drop characteristics

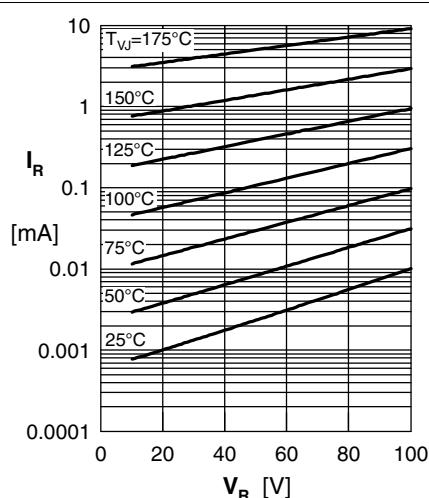


Fig. 2 Typ. reverse current I_R vs. reverse voltage V_R

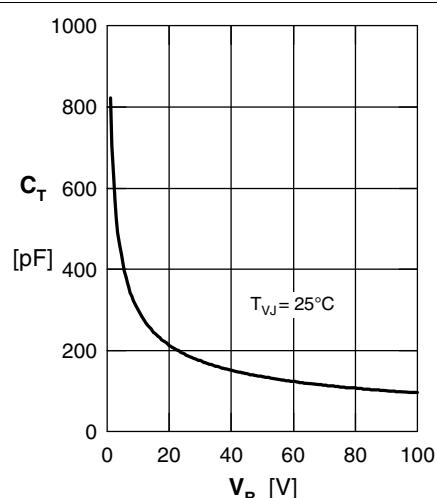


Fig. 3 Typ. junction capacitance C_T vs. reverse voltage V_R

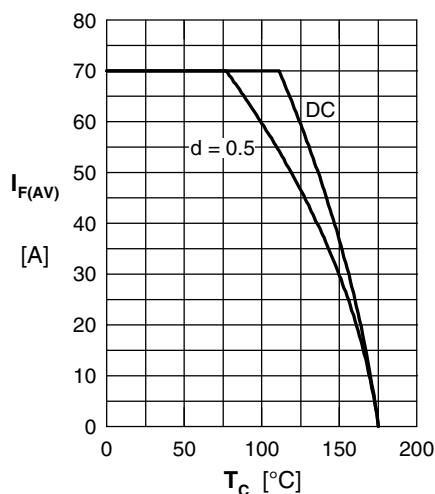


Fig. 4 Average forward current $I_{F(AV)}$ vs. case temperature T_C

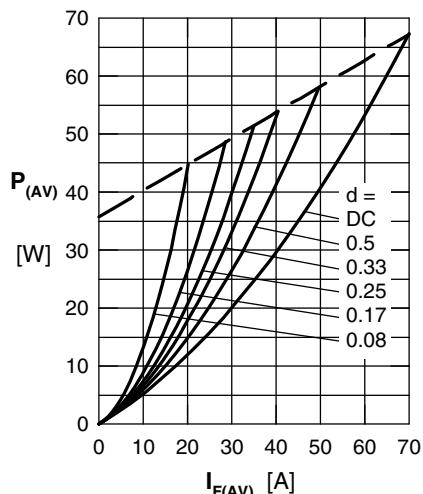


Fig. 5 Forward power loss characteristics

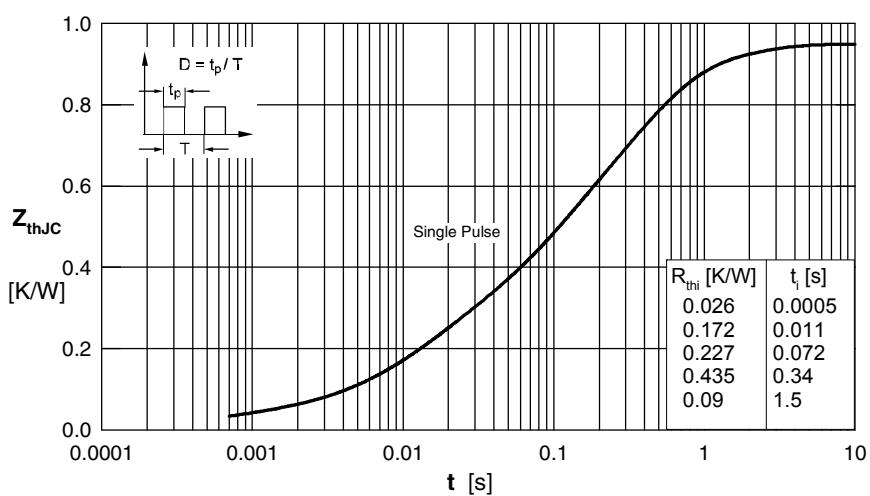


Fig. 6 Transient thermal impedance junction to case

Note: All curves are per diode